

# 10V Drive Nch MOSFET

# RCD040N25

#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) High-speed switching.
- 3) Wide range of SOA.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.

# Application

Switching

#### Packaging specifications

	Package	Taping
Type	Code	TL
	Basic ordering unit (pieces)	2500
RCD040N2	0	

## ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{DSS}$	250	V
Gate-source voltage		$V_{GSS}$	±30	V
Drain current	Continuous	I <sub>D</sub> *3	<u>±</u> 4	Α
	Pulsed	I <sub>DP</sub> *1,3	±16	Α
Source current	Continuous	I <sub>S</sub>	4	Α
(Body Diode)	Pulsed	I <sub>SP</sub> *1	16	Α
Avalanche current		I <sub>AS</sub> *2	2	Α
Avalanche energy		E <sub>AS</sub> *2	1.61	mJ
Power dissipation		P <sub>D</sub> *4	20	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C



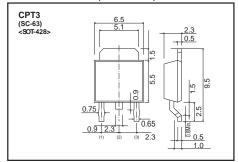
- \*2 L  $\stackrel{\bullet}{=}$  500 $\mu$ H,  $V_{DD}$ =50V,  $R_G$ =25 $\Omega$ ,  $T_{ch}$ =25 $^{\circ}$ C
- \*3 Limited only by maximum channel temperature allowed.
- \*4 T<sub>C</sub>=25°C

#### • Thermal resistance

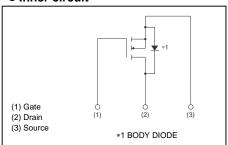
Parameter	Symbol	Limits	Unit
Channel to Case	Rth (ch-c)*	6.25	°C/W

<sup>\*</sup> T<sub>C</sub>=25°C

#### • Dimensions (Unit : mm)



#### • Inner circuit



<sup>\*</sup> Limited only by maximum channel temperature allowed.

# ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	1	-	±100	nA	$V_{GS}=\pm30V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	250	-	-	<b>V</b>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	1	-	10	μA	V <sub>DS</sub> =250V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	3.5	1	5.5	>	$V_{DS}$ =10V, $I_{D}$ =1mA
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	-	780	1000	mΩ	I <sub>D</sub> =2A, V <sub>GS</sub> =10V
Forward transfer admittance	I Y <sub>fs</sub> I*	1.2	-	-	S	$V_{DS}$ =10V, $I_{D}$ =2A
Input capacitance	C <sub>iss</sub>	1	410	-	рF	V <sub>DS</sub> =25V
Output capacitance	C <sub>oss</sub>	1	30	-	рF	V <sub>GS</sub> =0V
Reverse transfer capacitance	$C_{rss}$	1	15	-	рF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	1	17	-	ns	V <sub>DD</sub> ≒ 125V, I <sub>D</sub> =2A
Rise time	t <sub>r</sub> *	1	15	-	ns	V <sub>GS</sub> =10V
Turn-off delay time	t <sub>d(off)</sub> *	1	20	-	ns	$R_L=62.5\Omega$
Fall time	t <sub>f</sub> *	1	12	-	ns	$R_G=10\Omega$
Total gate charge	Q <sub>g</sub> *	-	9.0	-	nC	V <sub>DD</sub> ≒125V, I <sub>D</sub> =4A
Gate-source charge	Q <sub>gs</sub> *	-	3.5	-	nC	V <sub>GS</sub> =10V
Gate-drain charge	Q <sub>gd</sub> *	-	3.5	-	nC	$R_L=31.25\Omega$ $R_G=10\Omega$

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V <sub>SD</sub> *	-	-	1.5	V	I <sub>s</sub> =4A, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

#### ●Electrical characteristic curves (Ta=25°C)

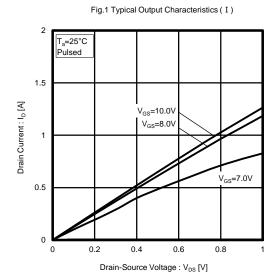


Fig.3 Typical Transfer Characteristics

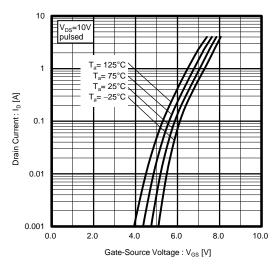


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

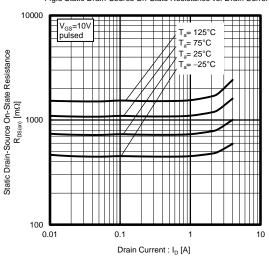


Fig.2 Typical Output Characteristics ( II )

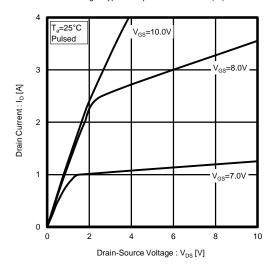


Fig.4 Gate Threshold Voltage vs. Channel Temperature

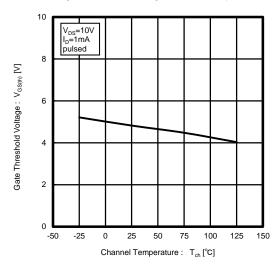


Fig.6 Static Drain-Source On-State Resistance vs. Channel Temperature

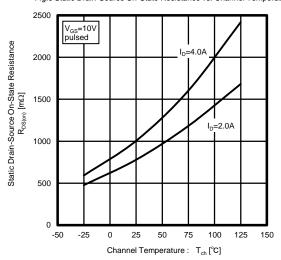


Fig.7 Forward Transfer Admittance vs. Drain Current

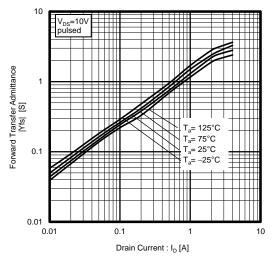


Fig.9 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

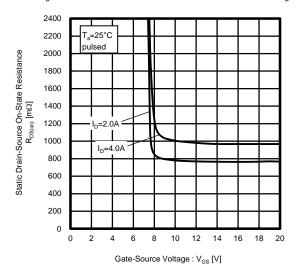


Fig.11 Dynamic Input Characteristics

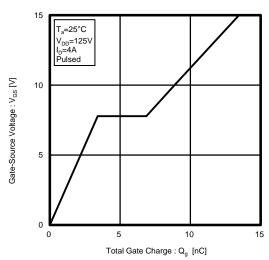


Fig.8 Source Current vs. Source-Drain Voltage

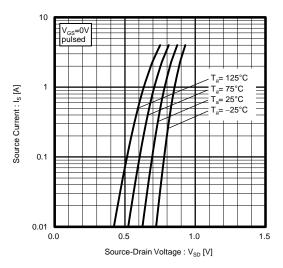


Fig.10 Switching Characteristics

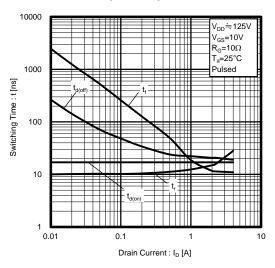


Fig.12 Typical Capacitance vs. Drain-Source Voltage

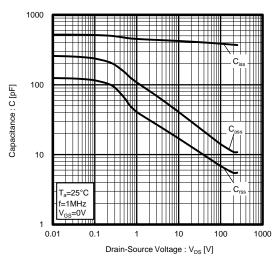
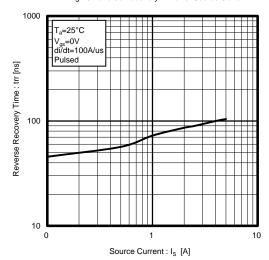


Fig.13 Reverse Recovery Time vs. Source Current



## Measurement circuits

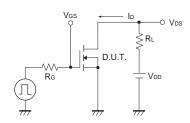


Fig.1-1 Switching Time Measurement Circuit

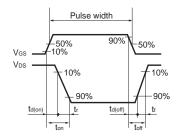


Fig.1-2 Switching Waveforms

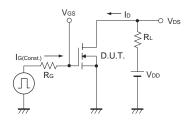


Fig.2-1 Gate Charge Measurement Circuit

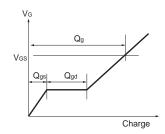


Fig.2-2 Gate Charge Waveform

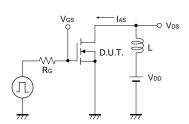


Fig.3-1 Avalanche Measurement Circuit

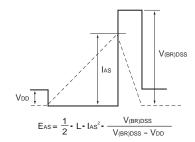


Fig.3-2 Avalanche Waveform

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